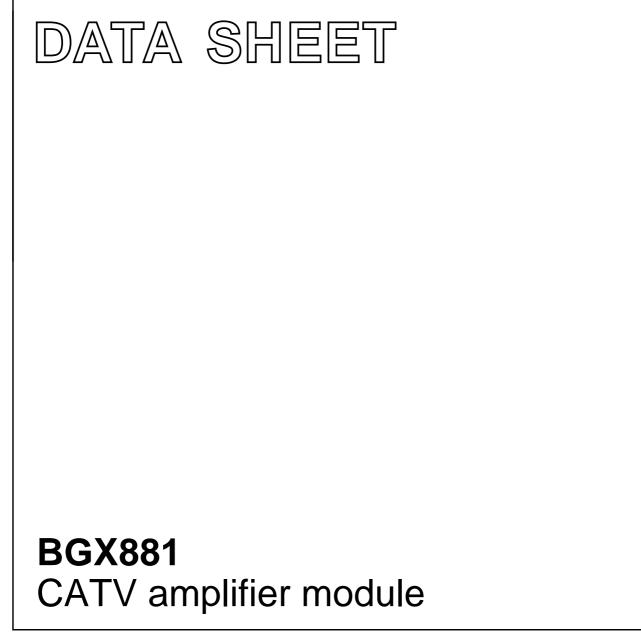
DISCRETE SEMICONDUCTORS



Product specification File under Discrete Semiconductors, SC16 February 1995

Philips Semiconductors





BGX881

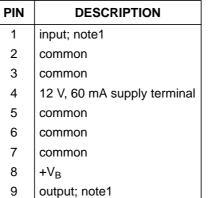
FEATURES

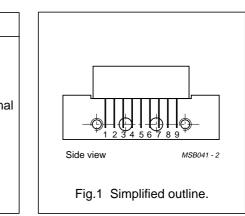
- Excellent linearity
- Extremely low noise
- Silicon nitride passivation
- Rugged construction
- Gold metallization ensures excellent reliability.

DESCRIPTION

Hybrid amplifier module for CATV/MATV systems operating over a frequency range of 40 to 860 MHz at a voltage supply of 24 V (DC).

QUICK REFERENCE DATA





SYMBOL PARAMETER CONDITIONS MIN. MAX. UNIT f = 50 MHz 12 13 dB Gp power gain total current consumption (DC) $V_{B} = 24 V$ 240 mΑ I_{tot}

1. Pins 1 and 9 carry DC voltages.

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

Note

SYMBOL	PARAMETER	MIN.	MAX.	UNIT
V _B	DC supply voltage	_	26	V
Vi	RF input voltage	-	65	dBmV
T _{stg}	storage temperature	-40	+100	°C
T _{mb}	operating mounting base temperature	-20	+100	°C

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CHARACTERISTICS

Bandwidth 40 to 860 MHz; V_B = 24 V; T_{mb} = 30 °C; Z_S = Z_L = 75 Ω .

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
G _p	power gain	f = 50 MHz	12	13	dB
SL	slope cable equivalent	f = 40 to 860 MHz	0.2	1.2	dB
FL	flatness of frequency response	f = 40 to 860 MHz	-	±0.3	dB
S ₁₁	input return losses	f = 40 MHz; note 1	20	-	dB
		f = 800 to 860 MHz	10	_	dB
S ₂₂	output return losses	f = 40 MHz; note 1	20	-	dB
		f = 640 to 860 MHz	15	_	dB
d ₂	second order distortion	note 2	-	-53	dB
Vo	output voltage	d _{im} = -60 dB; note 3	60.5	-	dBmV
		$d_{im} = -60 \text{ dB}; \text{ note } 4$	59.5	_	dBmV
F	noise figure	f = 350 MHz	_	8.5	dB
		f = 860 MHz	-	9	dB
I _{tot}	total current consumption (DC)	note 5	-	240	mA

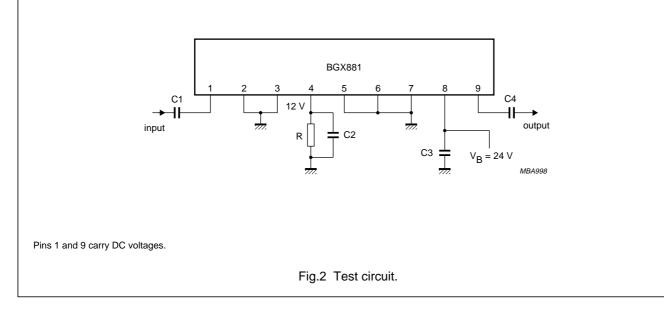
Notes

- 1. Decreases 1.5 dB per octave.
- 2. $f_p = 349.25 \text{ MHz}; V_p = 59 \text{ dBmV};$ $f_q = 403.25 \text{ MHz}; V_q = 59 \text{ dBmV};$ measured at $f_p + f_q = 752.5 \text{ MHz}.$
- 3. Measured according to DIN45004B: $f_p = 341.25 \text{ MHz}; V_p = V_o;$ $f_q = 348.25 \text{ MHz}; V_q = V_o -6 \text{ dB};$ $f_r = 350.25 \text{ MHz}; V_r = V_o -6 \text{ dB};$ measured at $f_p + f_q - f_r = 339.25 \text{ MHz}.$
- 4. Measured according to DIN45004B: $f_p = 851.25 \text{ MHz}; V_p = V_o;$ $f_q = 858.25 \text{ MHz}; V_q = V_o -6 \text{ dB};$ $f_r = 860.25 \text{ MHz}; V_r = V_o -6 \text{ dB};$ measured at $f_p + f_q - f_r = 849.25 \text{ MHz}.$
- 5. The module normally operates at $V_B = 24$ V, but is able to withstand supply transients up to 30 V.

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List of components (see Fig.2)

COMPONENT	DESCRIPTION	VALUE
C1, C3, C4	ceramic multilayer capacitor	1 nF
C2	ceramic multilayer capacitor	1 nF (max.)
R	resistor	200 Ω, 1 W



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DEFINITIONS

Data sheet status		
Objective specification	This data sheet contains target or goal specifications for product development.	
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.	
Product specification	This data sheet contains final product specifications.	
Limiting values		
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.		
Application information		

Where application information is given, it is advisory and does not form part of the specification.

LIFE SUPPORT APPLICATIONS

These products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Philips customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips for any damages resulting from such improper use or sale.